

Applicants respectfully direct the Examiner's attention to the first full paragraph on page 12 of the Specification, which discusses an exemplary embodiment of the invention which lacks metal chalcogenide agglomerations. Specifically, "[a]s compared to conventional prior art, a lower atomic percent incorporation is conducted within the chalcogenide material, and has been discovered in preferred embodiments to result in the elimination of surface agglomeration of Ag_2Se which is understood to have principally caused the discontinuous subsequent electrode formation of the prior art." The following paragraph beginning on page 12 and continuing on page 13 of the specification discusses another exemplary embodiment of the invention lacking metal chalcogenide agglomerations:

In this exemplary embodiment, interface region 25 is characterized by a higher content of "A" of the A_xB_y material as compared to the content of "A" in the first region 23. Apparently photodoping or other irradiation doping to the stated lower second thickness can result in greater driving of silver or other metal into germanium selenide or other glasses which can result in an outer germanium rich layer of the glass. This may facilitate a preferred lack of surface agglomeration of Ag_2Se .

Accordingly, the Specification supports the language added in the January 19 Amendment. Therefore, Applicants believe the pending application is in condition for allowance.

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Respectfully submitted,

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